

**9.6A, 500V, 0.600 Ohm, N-Channel Power MOSFET**

This is an N-Channel enhancement mode silicon gate power field effect transistor designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. This type can be operated directly from integrated circuits.

Formerly developmental type TA17435.

**Ordering Information**

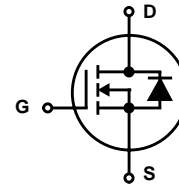
| PART NUMBER | PACKAGE  | BRAND |
|-------------|----------|-------|
| BUZ45       | TO-204AA | BUZ45 |

NOTE: When ordering, use the entire part number.

**Features**

- 9.6A, 500V
- $r_{DS(ON)} = 0.600\Omega$
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

**Symbol**



**Packaging**

JEDEC TO-204AA

